

isc Silicon NPN Power Transistor

2SC1569

DESCRIPTION

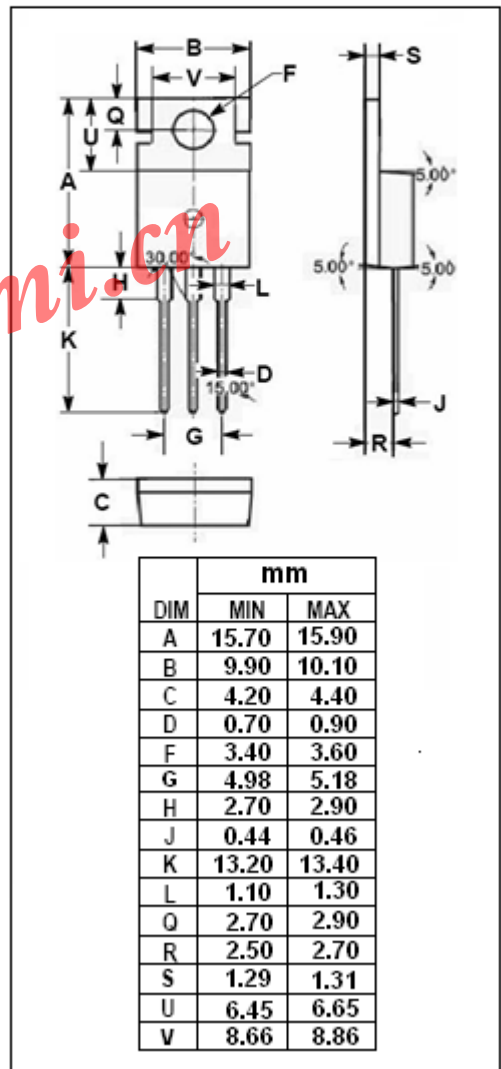
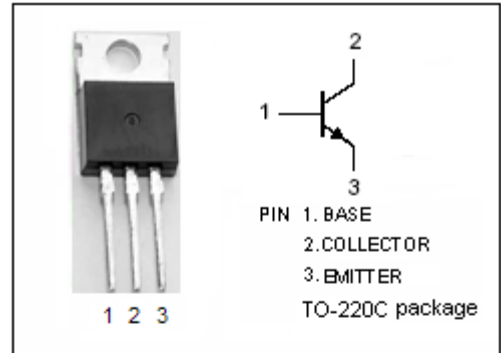
- High Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 300V(\text{Min})$
- DC Current Gain-
: $h_{FE} = 40-170 @ I_C = 50mA, V_{CE} = 10V$
- High Current-Gain Bandwidth Product

APPLICATIONS

- Designed for color TV chroma output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	150	mA
I_E	Emitter Current-Continuous	-150	mA
P_C	Collector Power Dissipation @ $T_a=25^\circ C$	1.5	W
	Collector Power Dissipation @ $T_c=25^\circ C$	12.5	
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=5\text{mA}; I_B=0$	300			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=100\text{mA}; I_B=20\text{mA}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=100\text{mA}; I_B=20\text{mA}$			1.2	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=100\text{V}; I_E=0$			1.0	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			1.0	μA
h_{FE}	DC Current Gain	$I_C=50\text{mA}; V_{CE}=10\text{V}$	40		170	
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=50\text{V}; f_{test}=1\text{MHz}$		5		pF
f_T	Current-Gain—Bandwidth Product	$I_C=30\text{mA}; V_{CE}=10\text{V}$	40			MHz